



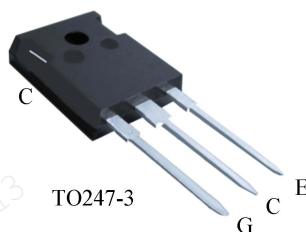
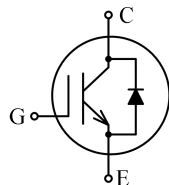
## BGNE40T65HD

IGBT in advanced TrenchFS Technology with soft and fast recovery anti-parallel diode  
具有先进 TrenchFS 技术的 IGBT 且反并联软快恢复二极管

### Features:

#### 特性

- 650V TrenchFS technology  
650V 沟槽栅场终止技术
- Low switching losses  
低开关损耗
- Positive temperature coefficient  
饱和电压正温度系数
- Short Circuit withstand time-5 $\mu$ s  
具备5 $\mu$ s短路承受能力



### Applications:

#### 应用

- UPS  
不间断电源
- PFC  
功率因数校正
- Welding  
焊机
- Industrial Power Supply  
工业电源

| Type<br>型号  | $V_{CE}[V]$<br>集电极-发射极电压 | $I_C[A]$<br>集电极电流 | $V_{CEsat}[V]$<br>饱和电压 | $T_{jmax}[^{\circ}C]$<br>最高结温 | Marking<br>标记 | Package<br>封装 |
|-------------|--------------------------|-------------------|------------------------|-------------------------------|---------------|---------------|
| BGNE40T65HD | 650                      | 40                | 1.85                   | 175                           | 40T65HD       | TO-247-3L     |



## BGNE40T65HD

### Maximum Rated Values

#### 最大额定参数

| Parameter<br>参数                                                                                                      | Symbol<br>符号 | Value<br>值       | Unit<br>单位       |
|----------------------------------------------------------------------------------------------------------------------|--------------|------------------|------------------|
| Collector-emitter voltage, $T_j \geq 25^\circ\text{C}$<br>集电极-发射极电压, $T_j \geq 25^\circ\text{C}$                     | $V_{CE}$     | 650              | V                |
| Collector current, $T_C = 25^\circ\text{C}$<br>集电极电流, $T_C = 25^\circ\text{C}$                                       | $I_C$        | 80               | A                |
| Collector current, $T_C = 100^\circ\text{C}$<br>集电极电流, $T_C = 100^\circ\text{C}$                                     | $I_C$        | 40               |                  |
| Pulsed collector current, $t_p$ limited by $T_{j\max}$<br>集电极脉冲电流, 脉宽时间受 $T_{j\max}$ 限制                              | $I_{Cpuls}$  | 160              |                  |
| Diode forward current, $T_C = 25^\circ\text{C}$<br>二极管正向电流, $T_C = 25^\circ\text{C}$                                 | $I_F$        | 80               |                  |
| Diode forward current, $T_C = 100^\circ\text{C}$<br>二极管正向电流, $T_C = 100^\circ\text{C}$                               | $I_F$        | 40               |                  |
| Diode pulsed current<br>二极管脉冲电流                                                                                      | $I_{Fpuls}$  | 160              | V                |
| Gate-emitter voltage<br>栅极-发射极电压                                                                                     | $V_{GE}$     | $\pm 20$         |                  |
| Short Circuit withstand time<br>$V_{GE} = 15\text{V}, V_{CC} \leq 400\text{V}, T_j \leq 150^\circ\text{C}$<br>短路耐受时间 | $t_{sc}$     | 5                |                  |
| Total power dissipation, $T_C = 25^\circ\text{C}$<br>总耗散功率, $T_C = 25^\circ\text{C}$                                 | $P_{tot}$    | 312.5            |                  |
| Maximum junction temperature<br>最高结温                                                                                 | $T_{j\max}$  | 175              |                  |
| Operating junction temperature<br>工作结温                                                                               | $T_{jop}$    | $-40 \dots +150$ | $^\circ\text{C}$ |
| Storage temperature<br>储存温度                                                                                          | $T_{stg}$    | $-55 \dots +150$ |                  |
| Soldering temperature, 1.6mm from case for 10s<br>焊接温度                                                               | $T_{st}$     | 260              |                  |
| Mounting Torque M3<br>锁装力矩                                                                                           | $M_d$        | 0.6              | Nm               |



## BGNE40T65HD

### Thermal Resistance

#### 热阻

| Parameter<br>参数                                         | Symbol<br>符号  | Value<br>值 | Unit<br>单位                  |
|---------------------------------------------------------|---------------|------------|-----------------------------|
| IGBT Thermal resistance junction to case<br>IGBT 结-管壳热阻 | $R_{th(j-c)}$ | 0.48       | $^{\circ}\text{C}/\text{W}$ |
| Diode Thermal resistance junction to case<br>二极管结-管壳热阻  | $R_{th(j-c)}$ | 0.54       | $^{\circ}\text{C}/\text{W}$ |
| Thermal resistance junction to ambient<br>结-环境热阻        | $R_{th(j-a)}$ | 40         | $^{\circ}\text{C}/\text{W}$ |

### Electrical Characteristic at $T_j = 25^{\circ}\text{C}$ (unless otherwise specified)

#### $T_j=25^{\circ}\text{C}$ 时电学特性（除非特别声明）

| Parameter<br>参数 | Symbol<br>符号 | Conditions<br>条件 | Value<br>值  |             |             | Unit<br>单位 |
|-----------------|--------------|------------------|-------------|-------------|-------------|------------|
|                 |              |                  | Min.<br>最小值 | Typ.<br>典型值 | Max.<br>最大值 |            |

### Static Characteristic

#### 静态特性

|                                                     |               |                                  |                    |      |      |     |         |
|-----------------------------------------------------|---------------|----------------------------------|--------------------|------|------|-----|---------|
| Collector-emitter breakdown voltage<br>集电极-发射极击穿电压  | $V_{(BR)CES}$ | $V_{GE}=0V,$<br>$I_C=100\mu A$   |                    | 650  | -    | -   | V       |
| Collector-emitter saturation voltage<br>集电极-发射极饱和电压 | $V_{cesat}$   | $V_{GE}=15V,$<br>$I_C=40A$       | $T_j=25^{\circ}C$  | -    | 1.85 | 2.2 |         |
|                                                     |               |                                  | $T_j=150^{\circ}C$ | -    | 2.1  | -   |         |
| Diode forward voltage<br>二极管正向电压                    | $V_F$         | $V_{GE}=0V,$<br>$I_F=40A$        | $T_j=25^{\circ}C$  | -    | 1.9  | 2.4 |         |
|                                                     |               |                                  | $T_j=150^{\circ}C$ | -    | 1.6  | -   |         |
| Gate-emitter threshold voltage<br>栅极-发射极阈值电压        | $V_{GE(th)}$  | $I_C=1mA,$<br>$V_{CE}=V_{GE}$    |                    | 5.0  | 5.8  | 7.0 |         |
| Collector-emitter cut-off current<br>集电极-发射极截止电流    | $I_{CES}$     | $V_{CE}=650V,$<br>$V_{GE}=0V$    |                    | -    | -    | 100 | $\mu A$ |
| Gate-emitter leakage current<br>栅极-发射极漏电流           | $I_{GES}$     | $V_{CE}=0V,$<br>$V_{GE}=\pm 20V$ |                    | -200 | -    | 200 | nA      |

### Dynamic Characteristic

#### 动态特性

|                            |           |                                                                |   |      |   |    |
|----------------------------|-----------|----------------------------------------------------------------|---|------|---|----|
| Input capacitance<br>输入电容  | $C_{ies}$ | $V_{CE}=25\text{V},$<br>$V_{GE}=0\text{V},$<br>$f=1\text{MHz}$ | - | 5200 | - | pF |
| Output capacitance<br>输出电容 | $C_{oes}$ |                                                                | - | 230  | - |    |



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|                                        |             |                                                                   |   |     |   |    |
|----------------------------------------|-------------|-------------------------------------------------------------------|---|-----|---|----|
| Reverse transfer capacitance<br>反向传输电容 | $C_{res}$   |                                                                   | - | 160 | - |    |
| Gate charge<br>门极电量                    | $Q_G$       | $V_{CC}=400V, I_C=40A,$<br>$V_{GE}=15V$                           | - | 238 | - | nC |
| Short circuit current<br>短路电流          | $I_{C(sc)}$ | $V_{CC}=400V, V_{GE}=15V,$<br>$tpsc \leq 5\mu s, T_j=150^\circ C$ | - | 230 | - | A  |

### Switching Characteristic at $T_j=25^\circ C$ (Inductive Load)

$T_j=25^\circ C$ 时开关特性（感性负载）

| Parameter<br>参数                 | Symbol<br>符号        | Conditions<br>条件                                                                                                                                                                                   | Value<br>值  |             |             | Unit<br>单位 |
|---------------------------------|---------------------|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-------------|-------------|-------------|------------|
|                                 |                     |                                                                                                                                                                                                    | Min.<br>最小值 | Typ.<br>典型值 | Max.<br>最大值 |            |
| IGBT Characteristic<br>IGBT 特性  |                     |                                                                                                                                                                                                    |             |             |             |            |
| Turn-on delay time<br>开通延迟时间    | t <sub>d(on)</sub>  | T <sub>j</sub> =25°C,<br>V <sub>CC</sub> =400V,<br>I <sub>C</sub> =40A,<br>V <sub>GE</sub> =-7.5/15V,<br>R <sub>G</sub> =10Ω,<br>Energy losses<br>include<br>“tail” and diode<br>reverse recovery. | -           | 100         | -           | ns         |
| Rise time<br>上升时间               | t <sub>r</sub>      |                                                                                                                                                                                                    | -           | 90          | -           |            |
| Turn-off delay time<br>关断延迟时间   | t <sub>d(off)</sub> |                                                                                                                                                                                                    | -           | 115         | -           |            |
| Fall time<br>下降时间               | t <sub>f</sub>      |                                                                                                                                                                                                    | -           | 25          | -           |            |
| Turn-on energy<br>开通损耗          | E <sub>on</sub>     |                                                                                                                                                                                                    | -           | 0.58        | -           | mJ         |
| Turn-off energy<br>关断损耗         | E <sub>off</sub>    |                                                                                                                                                                                                    | -           | 0.38        | -           |            |
| Total switching energy<br>总开关损耗 | E <sub>ts</sub>     |                                                                                                                                                                                                    | -           | 0.96        | -           |            |

### Anti-Parallel Diode Characteristic

反并联二极管特性

|                                           |           |                                                                        |   |      |   |         |
|-------------------------------------------|-----------|------------------------------------------------------------------------|---|------|---|---------|
| Reverse recovery time<br>反向恢复时间           | $t_{rr}$  | $T_j=25^\circ C,$<br>$V_R=400V,$<br>$I_F=40A,$<br>$diF/dt=1000A/\mu s$ | - | 55   | - | ns      |
| Recovered charge<br>恢复电荷                  | $Q_r$     |                                                                        | - | 1.8  | - | $\mu C$ |
| Peak reverse recovery current<br>反向恢复峰值电流 | $I_{RM}$  |                                                                        | - | 7    | - | A       |
| Reverse recovered energy<br>反向恢复损耗        | $E_{rec}$ |                                                                        | - | 0.07 | - | mJ      |



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### Switching Characteristic at $T_j=150^\circ\text{C}$ (Inductive Load)

$T_j=150^\circ\text{C}$ 时开关特性（感性负载）

| Parameter<br>参数                                | Symbol<br>符号        | Conditions<br>条件                                                                                                                                                                                    | Value<br>值      |                 |                 | Unit<br>单位 |
|------------------------------------------------|---------------------|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----------------|-----------------|-----------------|------------|
|                                                |                     |                                                                                                                                                                                                     | Min.<br>最小<br>值 | Typ.<br>典型<br>值 | Max.<br>最大<br>值 |            |
| IGBT Characteristic<br>IGBT 特性                 |                     |                                                                                                                                                                                                     |                 |                 |                 |            |
| Turn-on delay time<br>开通延迟时间                   | t <sub>d(on)</sub>  | T <sub>j</sub> =150°C,<br>V <sub>CC</sub> =400V,<br>I <sub>C</sub> =40A,<br>V <sub>GE</sub> =-7.5/15V,<br>R <sub>G</sub> =10Ω,<br>Energy losses<br>include<br>“tail” and diode<br>reverse recovery. | -               | 100             | -               | ns         |
| Rise time<br>上升时间                              | t <sub>r</sub>      |                                                                                                                                                                                                     | -               | 80              | -               |            |
| Turn-off delay time<br>关断延迟时间                  | t <sub>d(off)</sub> |                                                                                                                                                                                                     | -               | 135             | -               |            |
| Fall time<br>下降时间                              | t <sub>f</sub>      |                                                                                                                                                                                                     | -               | 65              | -               |            |
| Turn-on energy<br>开通损耗                         | E <sub>on</sub>     |                                                                                                                                                                                                     | -               | 0.83            | -               | mJ         |
| Turn-off energy<br>关断损耗                        | E <sub>off</sub>    |                                                                                                                                                                                                     | -               | 0.48            | -               |            |
| Total switching energy<br>总开关损耗                | E <sub>ts</sub>     |                                                                                                                                                                                                     | -               | 1.31            | -               |            |
| Anti-Parallel Diode Characteristic<br>反并联二极管特性 |                     |                                                                                                                                                                                                     |                 |                 |                 |            |
| Reverse recovery time<br>反向恢复时间                | t <sub>rr</sub>     | T <sub>j</sub> =150°C,<br>V <sub>R</sub> =400V,<br>I <sub>F</sub> =40A,<br>diF/dt=1000A/μs                                                                                                          | -               | 130             | -               | ns         |
| Recovered charge<br>恢复电荷                       | Q <sub>r</sub>      |                                                                                                                                                                                                     | -               | 2.1             | -               | μC         |
| Peak reverse recovery current<br>反向恢复峰值电流      | I <sub>RM</sub>     |                                                                                                                                                                                                     | -               | 12              | -               | A          |
| Reverse recovered energy<br>反向恢复损耗             | E <sub>rec</sub>    |                                                                                                                                                                                                     | -               | 0.11            | -               | mJ         |



## BGNE40T65HD

### ELECTRICAL CHARACTERISTICS

#### 特性曲线

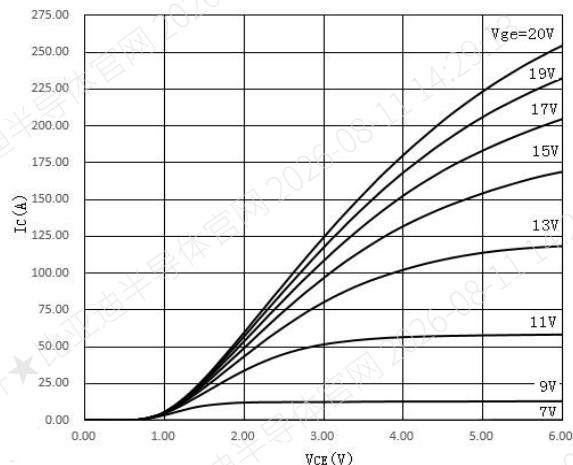


Figure 1. Typical output characteristic( $T_j=25^{\circ}\text{C}$ )

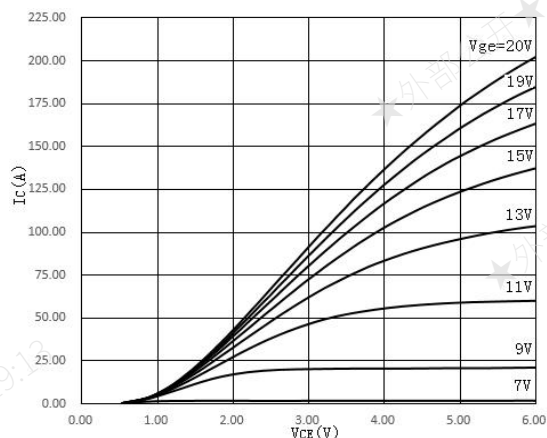


Figure 2. Typical output characteristic( $T_j=150^{\circ}\text{C}$ )

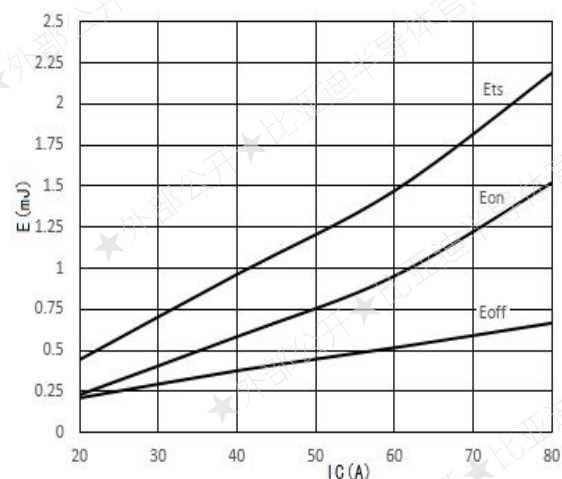


Figure 3. Switching energy vs  $I_c$   
( $T_j=25^{\circ}\text{C}$ ,  $V_{GE}=15\text{V}$ ,  $V_{CE}=400\text{V}$ ,  $R_g=10\ \Omega$ )

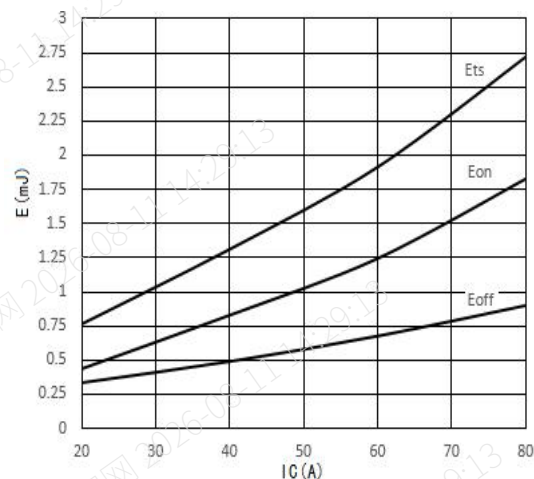


Figure 4. Switching energy vs  $I_c$   
( $T_j=150^{\circ}\text{C}$ ,  $V_{GE}=15\text{V}$ ,  $V_{CE}=400\text{V}$ ,  $R_g=10\ \Omega$ )

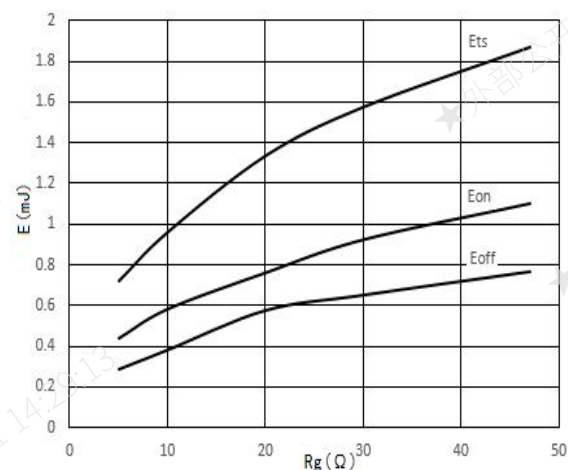


Figure 5. Switching energy losses vs  $R_g$   
( $T_j=25^{\circ}\text{C}$ ,  $V_{CE}=400\text{V}$ ,  $V_{GE}=15\text{V}$ ,  $I_c=40\text{A}$ )

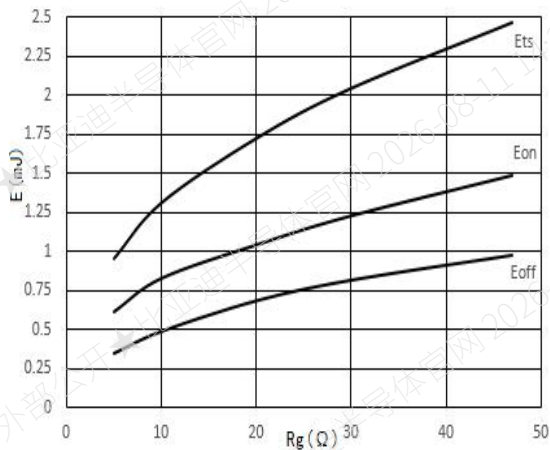


Figure 6. Switching energy losses vs  $R_g$   
( $T_j=150^{\circ}\text{C}$ ,  $V_{CE}=400\text{V}$ ,  $V_{GE}=15\text{V}$ ,  $I_c=40\text{A}$ )



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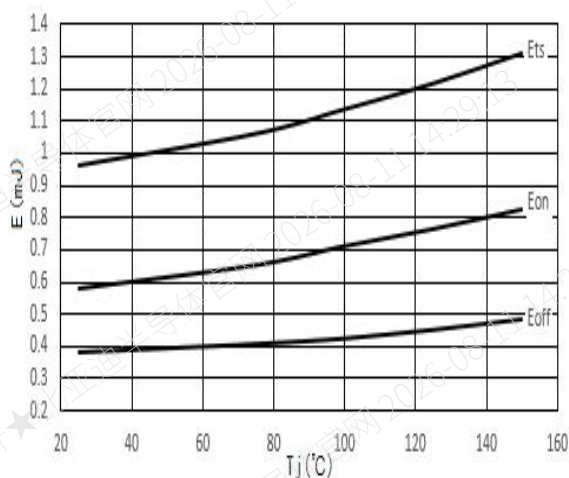


Figure 7. Switching energy losses vs Tj  
(VCE=400V, VGE=15V, IC=40A, RG=10Ω)

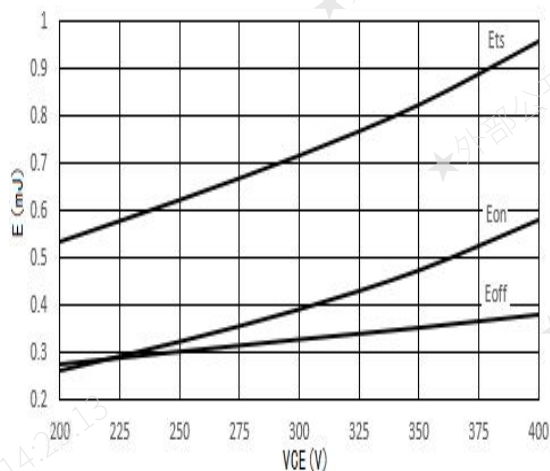


Figure 8. Switching energy losses vs VCE  
(Tj=25°C, VGE=15V, IC=40A, RG=10Ω)

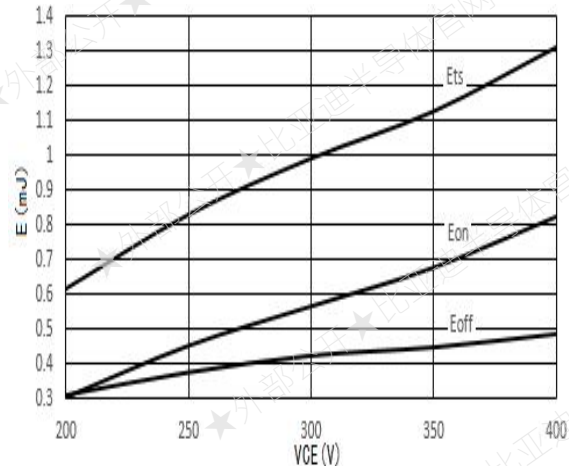


Figure 9. Switching energy losses vs VCE  
(Tj=150°C, VGE=15V, IC=40A, RG=10Ω)

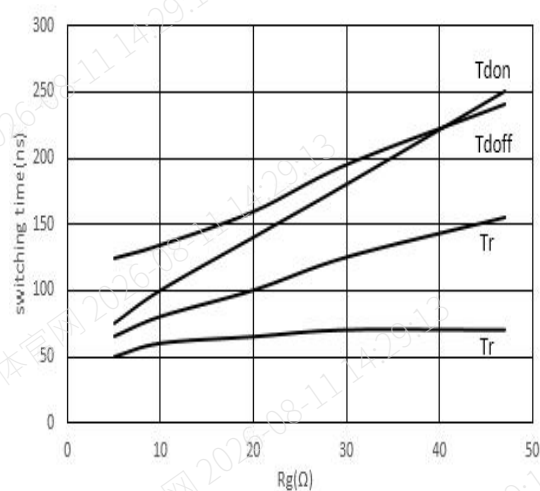


Figure 10. Switching times vs Rg  
(Tj=150°C, VCE=400V, VGE=15V, IC=40A)

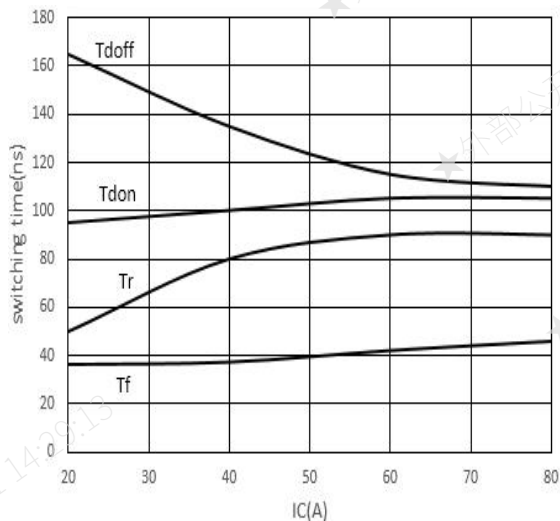


Figure 11. Switching times vs Ic  
(Tj=150°C, VCE=400V, VGE=15V, RG=10Ω)



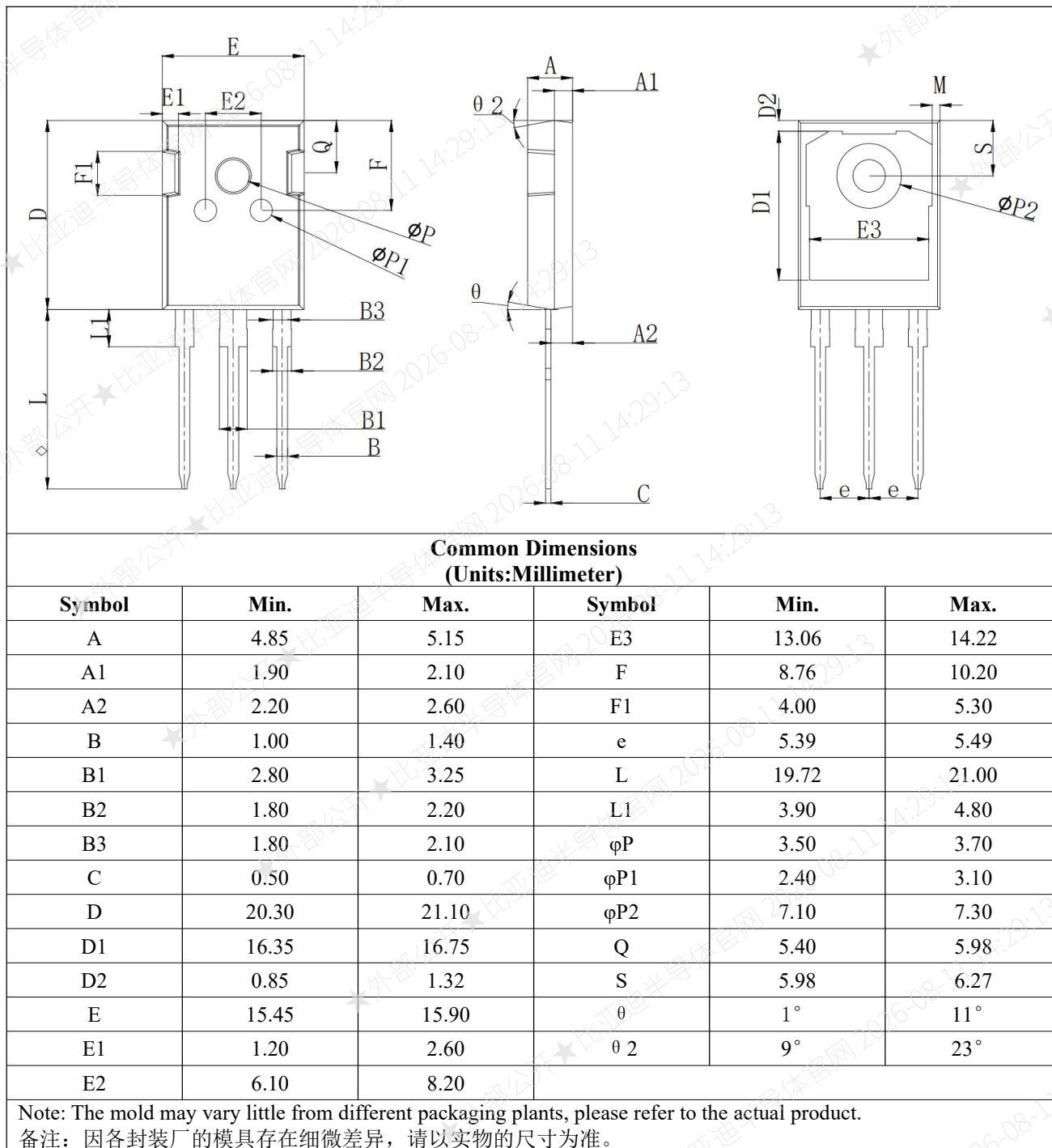
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## BGNE40T65HD

### TO-247-3L Outline Dimensions:

### TO-247-3L 外形尺寸



### Packing

### 包装

| Packing | pcs/tube | tube/ inner box | inner box/ carton | pcs/carton |
|---------|----------|-----------------|-------------------|------------|
| Tube    | 30       | 12              | 6                 | 2160       |



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- **Warranty Period:** Unless otherwise agreed in the COOPERATION AGREEMENT or other WRITTEN DOCUMENTS, the Warranty Period for products specified in this specification shall be one year from the date of purchase if the products are properly preserved.

Special instructions: Storage Temperature:  $20\pm 5^{\circ}\text{C}$ ; Relative Humidity: 30%-60%; The product should be stored in a place away from direct light and vibration.

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特殊说明: 储存温度:  $20\pm 5^{\circ}\text{C}$ ; 相对湿度: 30%-60%; 产品应放置于避光地方, 避免震动。

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